MSKSEMI















ESD

TVS

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SOT-143

Features

- 150Watts peak pulse power (tp = $8/20\mu s$)
- Tiny SOT143 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=1.5pF typ I/O to I/O.)
- Protection one data/power line to:
- IEC 61000-4-2 ±15kV contact ±20kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20µs)

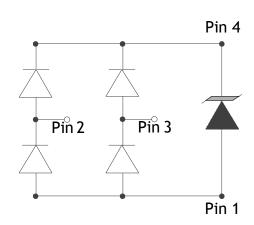
Mechanical Data

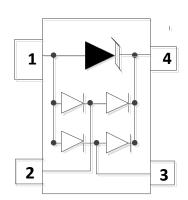
- SOT143 package
- Molding compound flammability rating: UL94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Applications

- USB2.0,
- Ethernet
- Notebooks, Desktops, and Servers
- Video Line Protection

Schematic & PIN Configuration







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Absolute Maximum Rating

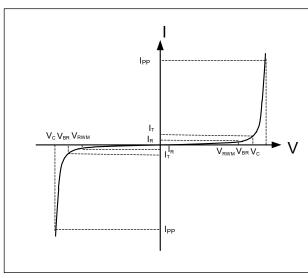
| Rating | Symbol | Value | Units |
|--|------------------|----------------|-------|
| Peak Pulse Power (t _p =8/20µs) | P _{PP} | 150 | Watts |
| Peak Pulse Current (t _p =8/20μs) (note1) | I _{pp} | 5 | А |
| ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact) | V _{ESD} | 20 15 | kV |
| Lead Soldering Temperature | T∟ | 260(10seconds) | C |
| Junction Temperature | TJ | -55 to + 125 | C |
| Storage Temperature | T _{stg} | -55 to + 125 | C |

Electrical Characteristics

| Parameter | Symbol | Conditions | Min | Typical | Max | Units |
|---------------------------|----------------|--|-----|---------|-----|-------|
| Reverse Stand-Off Voltage | V_{RWM} | | | | 5.5 | V |
| Reverse Breakdown Voltage | V_{BR} | I _T =1mA | 6.0 | | | V |
| Reverse Leakage Current | I _R | V _{RWM} =5V,T=25℃ | | | 500 | nA |
| Clamping Voltage | V _C | I _{PP} =5A,t _p =8/20μs | | 14 | | V |
| Junction Capacitance | C _j | V _R = 0V, f = 1MHz IO to IO | | 1.5 | | ~F |
| | | V _R = 0V, f = 1MHz IO to GND | | 1.0 | 2.0 | pF |

Electrical Parameters (TA = 25°C unless otherwise noted)

| Symbol | Parameter | | |
|-----------------|--|--|--|
| I PP | Maximum Reverse Peak Pulse Current | | |
| Vc | Clamping Voltage @ IPP | | |
| VRWM | Working Peak Reverse Voltage | | |
| IR | Maximum Reverse Leakage Current @ V _{RWM} | | |
| V _{BR} | Breakdown Voltage @ I⊤ | | |
| lτ | Test Current | | |
| | | | |
| | | | |



Note: 8/20µs pulse waveform.

CM1213A-02SR



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

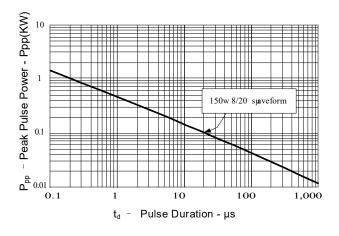


Figure 2: Power Derating Curve

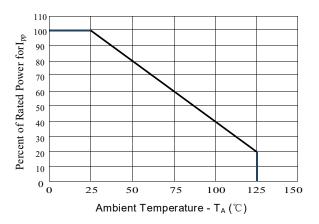


Figure3: Pulse Waveform

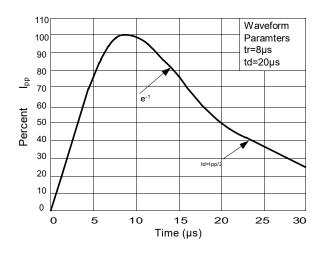
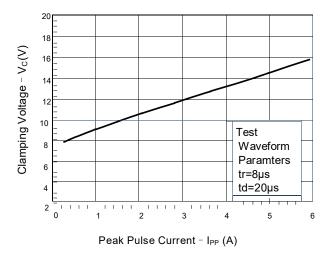
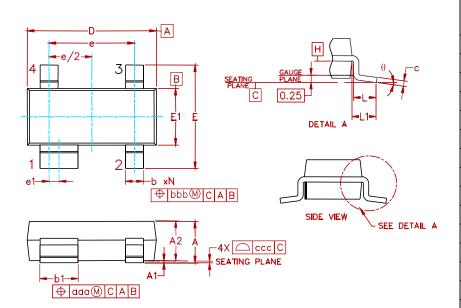


Figure 4: Clamping Voltage vs.lpp



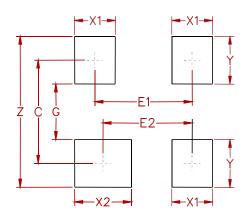


PACKAGE MECHANICAL DATA



| Symbol | Inches | | | Millimeters | | | |
|----------|---------|-------|-------|-------------|------|------|--|
| Syllibol | Min. | Nom. | Max. | Min. | Nom. | Max. | |
| Α | 0.031 | - | 0.048 | 0.80 | - | 1.22 | |
| A1 | 0.000 | - | 0.008 | 0.013 | - | 0.15 | |
| A2 | 0.020 | 0.035 | 0.042 | 0.75 | 0.90 | 1.07 | |
| b | 0.011 | - | 0.020 | 0.30 | - | 0.51 | |
| b1 | 0.029 | - | 0.037 | 0.76 | - | 0.94 | |
| С | 0.003 | - | 0.008 | 0.08 | - | 0.20 | |
| D | 0.110 | 0.114 | 0.120 | 2.80 | 2.90 | 3.04 | |
| E | 0.082 | 0.093 | 0.104 | 2.10 | 2.37 | 2.64 | |
| E1 | 0.047 | 0.051 | 0.055 | 1.20 | 1.30 | 1.40 | |
| e | 0.075 | | | 1.92 BSC | | | |
| e1 | 0.008 | | | 0.20 BSC | | | |
| L | 0.015 | 0.020 | 0.024 | 0.40 | 0.50 | 0.60 | |
| L1 | (0.021) | | | (0.54) | | | |
| N | 4 | | | 4 | | | |
| Ф | 0° | - | 8° | 0° | - | 8° | |
| aaa | 0.006 | | | | 0.15 | | |
| bbb | 0.008 | | | | 0.20 | | |
| ССС | 0.004 | | | | 0.10 | | |

Suggested Pad Layout



REEL SPECIFICATION

| P/N | PKG | QTY |
|--------------|---------|------|
| CM1213A-02SR | SOT-143 | 3000 |

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